

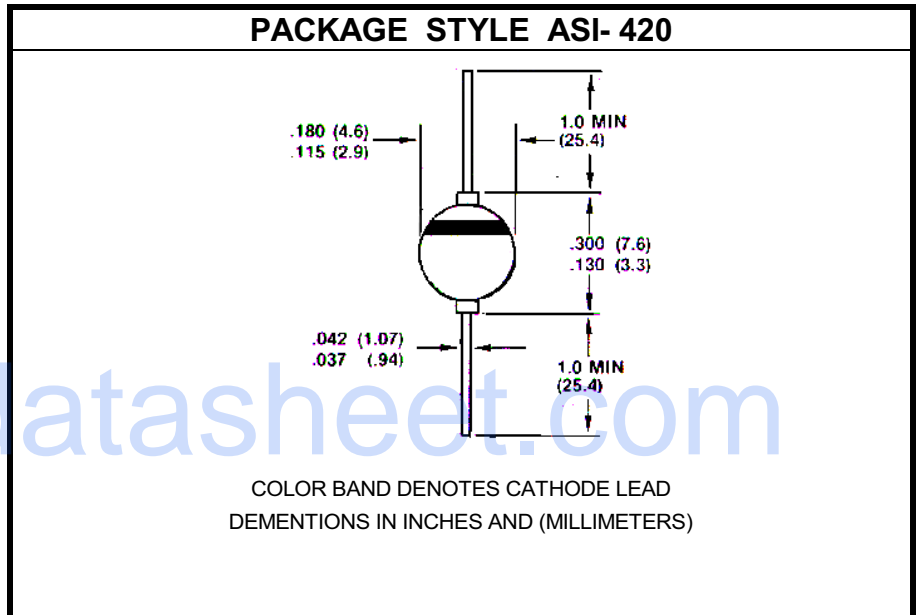
SILICON RECTIFIER-VERY FAST SWITCHING

DESCRIPTION:

The **1N5811** is Designed for General Purpose Very Fast Switching Applications.

MAXIMUM RATINGS

I_o	$I_F = 6.0 \text{ A (AVG) @ } T_L = 75 \text{ }^\circ\text{C/ L} = 3/8''$
V_{Rwm}	150 V
T_J	-65 $^\circ\text{C}$ to +175 $^\circ\text{C}$
T_{STG}	-65 $^\circ\text{C}$ to +175 $^\circ\text{C}$
θ_{JC}	18 $^\circ\text{C/W}$



CHARACTERISTICS $T_C = 25 \text{ }^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
I_R	$V_R = 150 \text{ V}$ $T_J = 100 \text{ }^\circ\text{C}$			5.0 150	μA
V_F	$I_F = 4.0 \text{ A}$			0.875	V
C_J	$V_R = 4.0 \text{ V}$ $f = 1.0 \text{ MHz}$		65		
t_{rr}	$I_F = 1.0 \text{ A}$ $I_R = 1.0 \text{ A}$ $I_{REC} = 0.1 \text{ A}$		15	30	nS
I_{FSM}	(Non repetitive) $t = 8.3 \text{ mS}$			125	A